

FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

| Ratings | Symbol | 2N3902 | 2N5157 | Units |
|---|----------------|-------------|--------|------------------|
| Collector-Emitter Voltage | V_{CEO} | 400 | 500 | Vdc |
| Emitter-Base Voltage | V_{EBO} | 5.0 | 6.0 | Vdc |
| Collector-Base Voltage | V_{CBO} | 700 | | Vdc |
| Collector Current | I_C | 3.5 | | Adc |
| Base Current | I_B | 2.0 | | Adc |
| Total Power Dissipation @ $T_A = 25^\circ\text{C}$ ⁽¹⁾ @ $T_A = 100^\circ\text{C}$ ⁽²⁾ | P_T | 5.0 | | W |
| | | 100 | | W |
| Operating & Storage Junction Temperature Range | T_J, T_{stg} | -65 to +200 | | $^\circ\text{C}$ |

THERMAL CHARACTERISTICS

| Characteristics | Symbol | Max. | Unit |
|--------------------------------------|-----------------|------|---------------------------|
| Thermal Resistance, Junction to Case | $R_{\theta JC}$ | 1.17 | $^\circ\text{C}/\text{W}$ |

- Derate linearly 29 mW/ $^\circ\text{C}$ for $T_A > 25^\circ\text{C}$
- Derate linearly 0.8 W/ $^\circ\text{C}$ for $T_C > 75^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

| Characteristics | Symbol | Min. | Max. | Unit |
|--|----------------|------|------|-----------------|
| OFF CHARACTERISTICS | | | | |
| Collector-Emitter Cutoff Current ($V_{CE} = 325\text{V}$) ($V_{CE} = 400\text{V}$) | 2N3902 | - | 250 | μAdc |
| | 2N5157 | | 250 | |
| Collector-Emitter Cutoff Current ($V_{BE} = 1.5\text{V}, V_{CE} = 700\text{V}$) | I_{CEX} | | 500 | μAdc |
| Emitter-Base Cutoff Current ($V_{EB} = 5.0$) ($V_{EB} = 6.0$) | 2N3902 | - | 200 | μAdc |
| | 2N5157 | | 200 | |
| ON-CHARACTERISTICS⁽³⁾ | | | | |
| Base-Emitter Saturation Voltage ($I_C = 1.0\text{A}, I_B = 0.1\text{A}$) ($I_C = 3.5\text{A}, I_B = 0.7\text{A}$) | $V_{BE(sat)}$ | - | 1.5 | Vdc |
| | | - | 2.0 | |
| Collector-Emitter Saturation Voltage ($I_C = 1.0\text{A}, I_B = 0.1\text{A}$) ($I_C = 3.5\text{A}, I_B = 0.7\text{A}$) | $V_{CE(sat)}$ | - | 0.8 | Vdc |
| | | - | 2.5 | |
| Forward Current Transfer Ratio ($I_C = 0.5\text{A}, V_{CE} = 5.0\text{V}$) ($I_C = 1.0\text{A}, V_{CE} = 5.0\text{V}$) ($I_C = 2.5\text{A}, V_{CE} = 5.0\text{V}$) ($I_C = 3.5\text{A}, V_{CE} = 5.0\text{V}$) | h_{FE} | 25 | - | - |
| | | 30 | 90 | |
| | | 10 | - | |
| | | 5 | - | |
| Collector-Emitter Sustaining Voltage ($I_C = 100\text{mA}$) | $V_{CEO(sus)}$ | 325 | - | Vdc |
| | | 400 | - | |

2N3902, 2N5157

NPN HIGH POWER SILICON TRANSISTORS

| Characteristics | Symbol | Min. | Max. | Unit |
|--|-----------|------|------|---------------|
| DYNAMIC CHARACTERISTICS | | | | |
| Small Signal Short Circuit Forward Current Transfer Ratio ($I_C = 0.2A, V_{CE} = 10V, f = 1\text{ MHz}$) | h_{FEI} | 2.5 | 25 | - |
| Output Capacitance ($V_{CB} = 10V, I_E = 0, 100\text{ kHz} \leq f \leq 1\text{ MHz}$) | C_{obo} | - | 250 | pF |
| SWITCHING CHARACTERISTICS | | | | |
| Turn-On Time ($V_{CC} = 125V, I_C = 1.0A, I_{B1} = 0.1A$) | t_{on} | - | 0.8 | μS |
| Turn-Off Time ($V_{CC} = 125V, I_C = 1.0A, I_{B1} = 0.1A, -I_{B2} = 0.5A$) | t_{off} | - | 1.7 | μS |
| SAFE OPERATING AREA | | | | |
| DC Tests (continuous) $T_C = 25^\circ\text{C}, t \geq 1.0\text{s}$ | | | | |
| Test 1 $V_{CE} = 28.6V, I_C = 3.5A$ | | | | |
| Test 2 $V_{CE} = 70V, I_C = 1.43A$ | | | | |
| Test 3 $V_{CE} = 325V, I_C = 55A$ (2N3902) $V_{CE} = 400V, I_C = 35A$ (2N5157) | | | | |
| Switching Tests | | | | |
| Load Condition C (unclamped inductive load) $T_C = 25^\circ\text{C}, \text{duty cycle} \leq 10\%, R_S = 0.1\Omega$ | | | | |
| Test 1 $t_p = \text{approximately } 3\text{ms}(\text{vary to obtain } I_C), R_{BB1} = 20\Omega, V_{BB1} = 10V, R_{BB2} = 3\text{k}\Omega, V_{BB2} = 1.5V, V_{CC} = 50V, I_C = 3.5A, L = 60\text{mH}, R = 3\Omega, R_L \leq 14\Omega$ | | | | |
| Test 2 $t_p = \text{approximately } 3\text{ms}(\text{vary to obtain } I_C), R_{BB1} = 100\Omega, V_{BB1} = 10V, R_{BB2} = 3\text{k}\Omega, V_{BB2} = 1.5V, V_{CC} = 50V, I_C = 0.6A, L = 200\text{mH}, R = 8\Omega, R_L \leq 83\Omega$ | | | | |
| Switching Tests | | | | |
| Load Condition C (clamped inductive load) $T_C = 25^\circ\text{C}, \text{duty cycle} \leq 10\%$ | | | | |
| Test 1 $t_p = \text{approximately } 30\text{ms}(\text{vary to obtain } I_C), R_S = 0.1\Omega, R_{BB1} = 20\Omega, V_{BB1} = 10V, R_{BB2} = 100\Omega, V_{BB2} = 1.5V, V_{CC} = 50V, I_C = 3.5A, L = 60\text{mH}, R = 3\Omega, R_L \leq 0\Omega$ (A suitable clamping circuit or diode can be used) Clamp voltage = 400+0, -5V (2N3902) Clamp voltage = 500+0, -5V (2N5157) Clamped voltage must be reached | | | | |

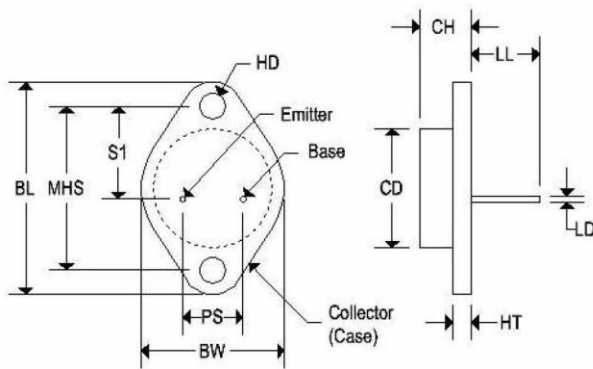
3. Pulse Test : Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$

2N3902, 2N5157

NPN HIGH POWER SILICON TRANSISTORS

MECHANICAL CHARACTERISTICS

| | |
|------------------|---------------|
| Case: | TO-3 |
| Marking: | Alpha-Numeric |
| Polarity: | See below |



| | TO-3 | | | |
|-----|-----------|-------|-------------|--------|
| | Inches | | Millimeters | |
| | Min | Max | Min | Max |
| CD | - | 0.875 | - | 22.220 |
| CH | 0.250 | 0.380 | 6.860 | 9.650 |
| HT | 0.060 | 0.135 | 1.520 | 3.430 |
| BW | - | 1.050 | - | 26.670 |
| HD | 0.131 | 0.188 | 3.330 | 4.780 |
| LD | 0.038 | 0.043 | 0.970 | 1.090 |
| LL | 0.312 | 0.500 | 7.920 | 12.700 |
| BL | 1.550 REF | | 39.370 REF | |
| MHS | 1.177 | 1.197 | 29.900 | 30.400 |
| PS | 0.420 | 0.440 | 10.670 | 11.180 |
| S1 | 0.655 | 0.675 | 16.640 | 17.150 |